

Application No. 10/058.116

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A semiconductor device, comprising:
a semiconductor film;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film.
2. (Previously Presented) A semiconductor device, comprising:
a semiconductor film having a source region and a drain region;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, a width of the gate electrode being smaller than a width of the semiconductor film.
3. (Previously Presented) The semiconductor device according to Claim 1, further comprising a sub gate electrode connected to the gate electrode.
4. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed on the gate electrode.
5. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed so as to cover at least one end of the semiconductor film.
- 6-8. (Canceled).
9. (Currently Amended) A semiconductor device, comprising:
a semiconductor film having a plurality of source regionregions and a drain regionregions, the semiconductor film including a plurality of regions formed of an intrinsic semiconductor which is not doped with dopant;

Application No. 10/058,116

a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film; and
_____ the regions extending toward at least one of the plurality of source
regionregions and the drain regionregions from the gate electrode and separating adjacent
source regions and adjacent drain regions.

10. (Previously Presented) The semiconductor device according to Claim 1,
the semiconductor film being formed on an insulating layer.
11. (Previously Presented) A circuit board, comprising:
the semiconductor device according to Claim 1; and
wires that supply at least one of signals and electric power to the
semiconductor device.
12. (Previously Presented) An electro-optical device, comprising:
the circuit board according to Claim 11;
a first electrode formed above the circuit board; and
an electro-optical element formed above the first electrode.
13. (Previously Presented) An electro-optical device, comprising:
an electro-optical element; and
the semiconductor device according to Claim 1, the electro-optical element
and the semiconductor device being used as at least one electronic circuit selected from the
group consisting of shift registers, level shifters, buffer circuits, and analog switches.
14. (Previously Presented) The electro-optical device according to Claim 12, the
electro-optical element being an organic electroluminescence element.
15. (Previously Presented) An electronic apparatus, comprising:
the electro-optical device according to Claim 12, the electro-optical device
being used as a display.